

Silicon NPN transistor epitaxial type CP041

[Applications]

General purpose

[Feature]

Low collector saturation voltage $V_{CE(sat)} = 0.5V(\text{Max.})$ at $I_C = 50\text{mA}$, $I_B = 5\text{mA}$

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	120	V
Collector-emitter voltage	VCEO	120	V
Emitter-base voltage	VEBO	5	V
Collector current	IC	50	mA
Junction temperature	Tj	125	C
Storage temperature	Tstg	-55 to 125	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	120	-	-	V	$I_C = 50\mu\text{A}$, $I_E = 0\text{A}$
Collector-emitter breakdown voltage	BVCEO	120	-	-	V	$I_C = 1\text{mA}$, $I_B = 0\text{A}$
Emitter-base breakdown voltage	BVEBO	5	-	-	V	$I_E = 50\mu\text{A}$, $I_C = 0\text{A}$
Collector cutoff current	ICBO	-	-	500	nA	$V_{CB} = 100\text{V}$
Emitter cutoff current	IEBO	-	-	500	nA	$V_{EB} = 4\text{V}$
DC current gain	hFE	180	-	560	-	$V_{CE} = 6\text{V}$, $I_C = 2\text{mA}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	0.5	V	$I_C = 50\text{mA}$, $I_B = 5\text{mA}$
Transition frequency	fT	-	140	-	MHz	$V_{CE} = 12\text{V}$, $I_E = -2\text{mA}$
Collector output capacitance	Cob	-	3.2	-	pF	$V_{CB} = 12\text{V}$, $f = 1\text{MHz}$, $I_E = 0\text{A}$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.